

TDC development for future detectors

Initial technology evaluation

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Motivation

DOE Basic Research Needs Study on High Energy Physics Detector Research and Development

- Future high energy, high luminosity hadron colliders will present much higher levels of pileup and extreme radiation environments
- Future detectors will require higher segmentation (3D position resolution) and additional time resolving capabilities while sustaining higher radiation doses (**Instrumentation BRN – Science Driver: Higgs and the energy frontier - PRD10, PRD16, PRD17, PRD18, PRD19, PRD20**)
- To satisfy requirements front-end sensors and readout ASICs will need to be compatible with:
 - Larger channel density – Low power, Smaller feature size (Deep sub-micron technologies)
 - Precision timing resolution – fast sensors, in pixel high precision timing circuits
 - Unprecedented radiation levels (dose of up to 30 GRad and 10^{18} neutrons/cm²)

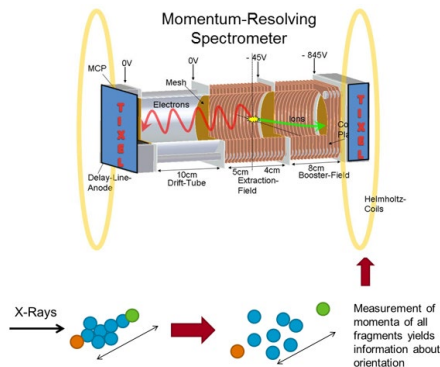
Basic Research Needs for High Energy Physics Detector Research & Development		
	PRD: Priority Research Direction	Grand Challenge
Calorimetry	PRD 1: Enhance calorimetry energy resolution for precision electroweak mass and missing-energy measurements	1
	PRD 2: Advance calorimetry with spatial and timing resolution and radiation hardness to master high-rate environments	1,4
	PRD 3: Develop ultrafast media to improve background rejection in calorimeters and particle identification detectors	1,3,4
Nobles	PRD 4: Enhance and combine existing modalities to increase signal-to-noise and reconstruction fidelity	1,2
	PRD 5: Develop new modalities for signal detection	1
	PRD 6: Improve the understanding of detector microphysics and characterization	1
Photodetectors	PRD 7: Extend wavelength range and develop new single-photon counters to enhance photodetector sensitivity	1,3
	PRD 8: Advance high-density spectroscopy and polarimetry to extract all photon properties	2,3
	PRD 9: Adapt photosensors for extreme environments	2,4
Quantum	PRD 10: Design new devices and architectures to enable picosecond timing and event separation	1,2,4
	PRD 11: Develop new optical coupling paradigms for enhanced or dynamic light collection	1,2,3
	PRD 12: Advance quantum devices to meet and surpass the Standard Quantum Limit	1,3
ASIC	PRD 13: Enable the use of quantum ensembles and sensor networks for fundamental physics	1,2
	PRD 14: Advance the state of the art in low-threshold quantum calorimeters	1,3
	PRD 15: Advance enabling technologies for quantum sensing	1,2,3
SolidState	PRD 16: Develop process evaluation and modeling for ASICs in extreme environments	3,4
	PRD 17: Create building blocks for Systems-on-Chip for extreme environments	1,4
	PRD 18: Develop high spatial resolution pixel detectors with precise high per-pixel time resolution to resolve individual interactions in high-collision-density environments	1,4
TDAQ	PRD 19: Adapt new materials and fabrication/integration techniques for particle tracking	2,3
	PRD 20: Realize scalable, irreducible-mass trackers	2,3
	PRD 21: Achieve on-detector, real-time, continuous data processing and transmission to reach the exascale	2,4
Xcut	PRD 22: Develop technologies for autonomous detector systems	2
	PRD 23: Develop timing distribution with picosecond synchronization	1
	PRD 24: Manipulate detector media to enhance physics reach	1,3
	PRD 25: Advance material purification and assay methods to increase sensitivity	1,2,3,4
	PRD 26: Addressing challenges in scaling technologies	2,3

Timing ASICs @ SLAC

TID-ID **SLAC**

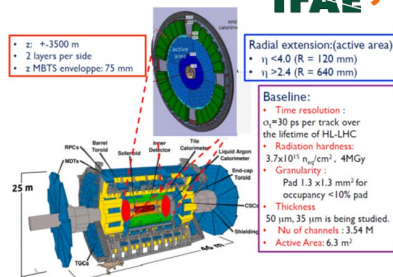
Tixel (SparkPix family)

- Application: **Photon Science**
- Detector Type: **Hybrid PAD**
- Sensor: **Thin Si**
- ASIC Technology: **0.13 μ m**
- Resolution: **100ps**
- Pixel: **100x100 μ m²**
- TDC area: **85x45 μ m²**
- TDC DR: **16bits (4 + 4 + 8) - 1 μ s**
- TDC Power: **16 μ W**



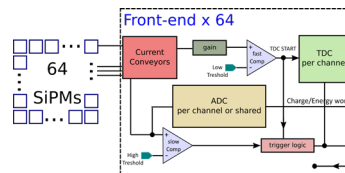
HGTD (Altiroc)

- Application: **HEP**
- Detector Type: **Hybrid PAD**
- Sensor: **LGAD**
- ASIC Technology: **0.13 μ m**
- Resolution: **20ps**
- Pixel: **1.3x1.3mm²**
- TDC area: **210x430 μ m²**
- TDC DR: **7bits (5 + 2) – 2.56ns**
- TDC Power: **460 μ W (10% occupancy)**



SiPM ToF PET

- Application: **Nuclear Medicine**
- Detector Type: **Hybrid**
- Sensor: **SiPM**
- ASIC Technology: **0.13 μ m**
- Resolution: **10ps**
- Channel width: **250 μ m (64 channels)**
- TDC area: **450x430 μ m²**
- TDC DR: **11bits (5+2+4) – 20ns**
- TDC Power: **650 μ W (10% occupancy)**



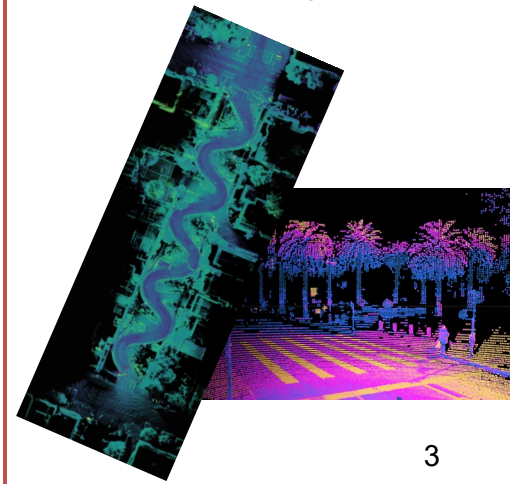
Stanford
MEDICINE



DEI DIPARTIMENTO DI
INGEGNERIA ELETTRICA
E DELL'INFORMAZIONE

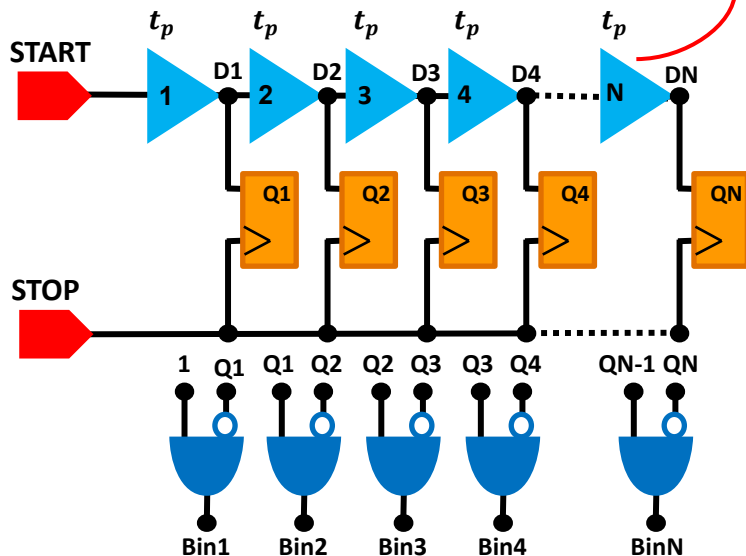
ToF LiDAR (CRADA)

- Application: **Automotive**
- Detector Type: **Monolithic**
- Sensor: **SPAD**
- ASIC Technology: **0.13 μ m HV**
- Resolution: **1ns**
- Channel width: **400 μ m (80 channels)**
- TCSPC area: **200x140 μ m²**
- TDC DR: **10bits**
- TCSPC Power: **1000 μ W**



Delay Line TDC

- Majority of modern TDCs is based on some version of a delay-line structure:

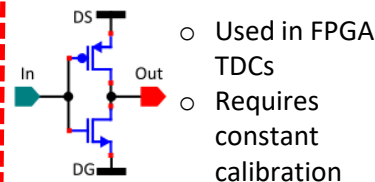


- TDC resolution given by the propagation delay of the elementary cell:

$$LSB_{TDC} = t_p$$

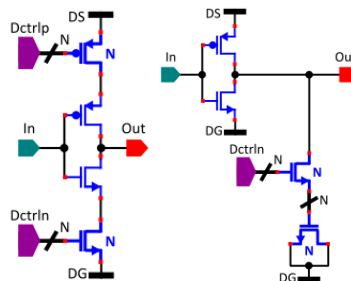
- Basic element: **Delay Cell**

Simple Logic Gate:



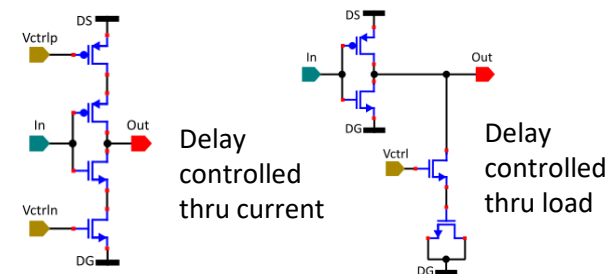
- Used in FPGA TDCs
- Requires constant calibration

Digitally-Controlled Delay Cell:

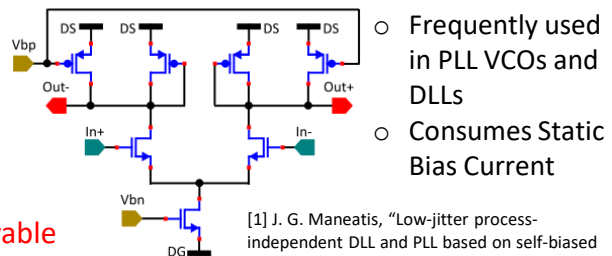


Voltage-Controlled Delay Cell:

- Current starved:
- Shunt capacitor:



- Differential delay cell with symmetric loads (Maneatis cell [1]):



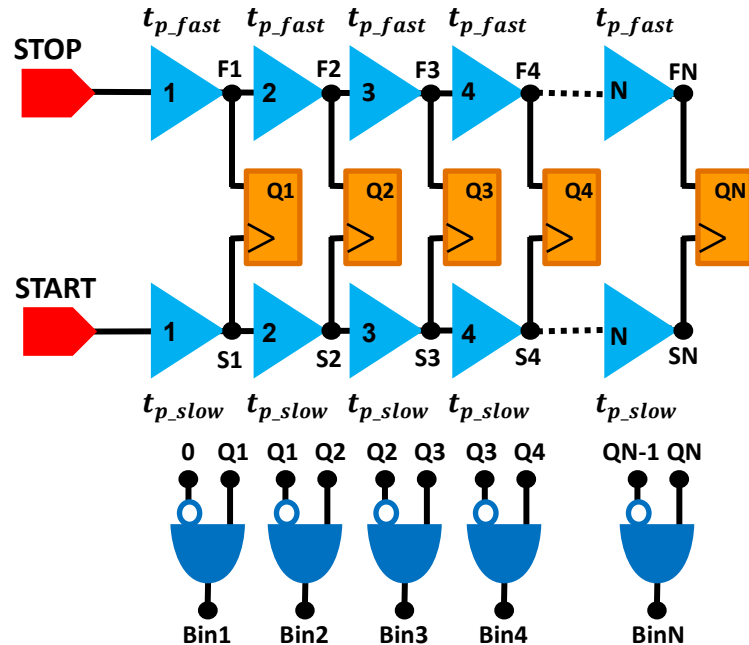
- Frequently used in PLL VCOs and DLLs
- Consumes Static Bias Current

Minimum delay limited by fastest achievable logic propagation delay in target technology

[1] J. G. Maneatis, "Low-jitter process-independent DLL and PLL based on self-biased techniques," IEEE J. Solid-State Circuits, vol. 31, no. 11, pp. 1723–1732, Nov. 1996.

Vernier Delay Line TDC

- ❑ What if resolutions lower than minimum propagation delay is required? → Vernier Delay Line



$$LSB_{TDC} = t_{p_slow} - t_{p_fast}$$

- ❑ **START** signal propagates in the **Slow Delay Line** ($t_{p_slow} > t_{p_fast}$)
- ❑ **STOP** signal propagates in the **Fast Delay Line**
- The **START** pulse comes first and initializes the TDC operation.
 - The **STOP** pulse follows the **START** with a delay that represents the time interval to be digitalized.
 - At each tap of the Delay Line the **STOP** signal catches up to the **START** signal by the difference of the propagation delays of cells in Slow and Fast branches, i.e., $t_{p_slow} - t_{p_fast}$ represents the **LSB** of time measurement.
 - The number of cells necessary for **STOP** signal to surpass the **START** signal represents the result of TDC conversion.

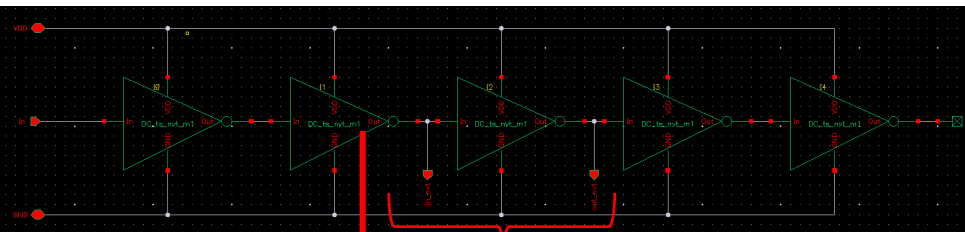
Compare to the simple Delay Line, Vernier Delay Line allows for TDC resolutions below the minimum logic propagation delay in the technology but suffer from higher power and area consumption and slower conversion times.



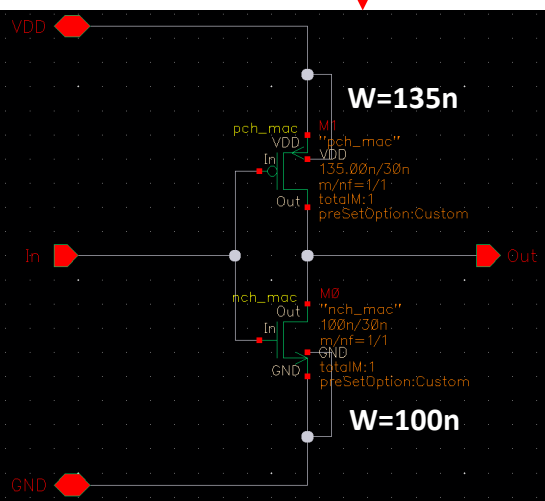
Studying the logic propagation delay in the technology necessary for defining the TDC architecture

Testbench: Minimum Propagation Delay

Delay Line Testbench:



Inverter as a Delay Cell:



t_p - Cell Propagation Delay

SVT, LVT, HVT

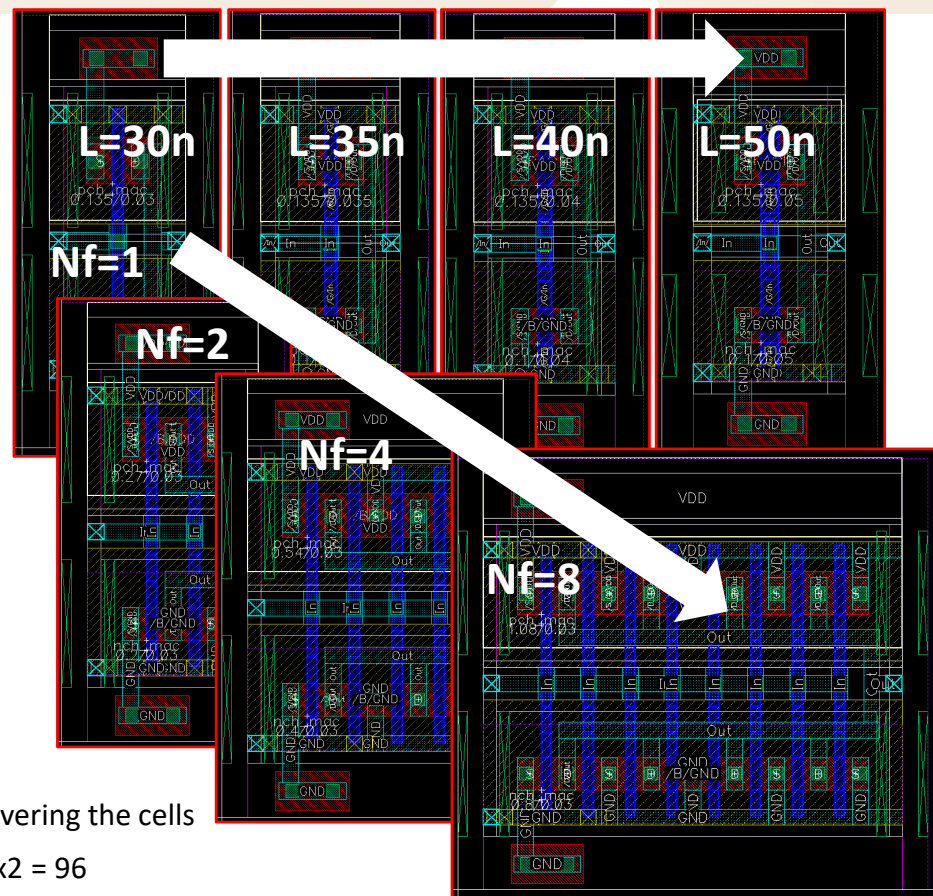
Simulations: Spectre

- **SCH** – Schematic
- **RCX** – Parasitic Extracted

Extraction: Calibre PEX

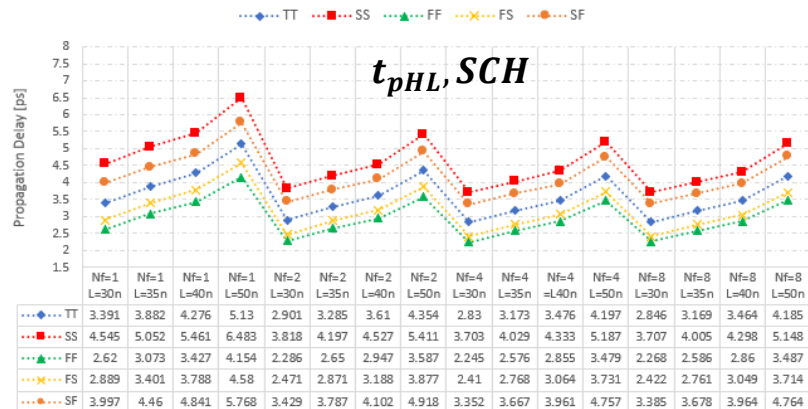
- M1 – Signal Connections
- M2 – VDD & GND planes covering the cells

Total Number of Views: $4 \times 4 \times 3 \times 2 = 96$

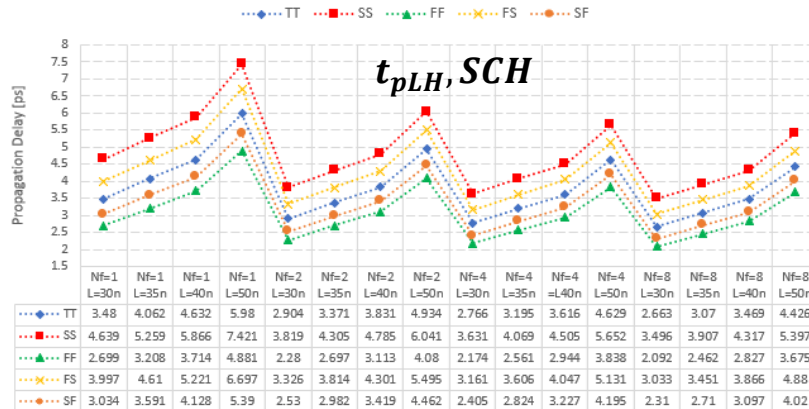


SVT Propagation Delay: HL / LH VS Corners

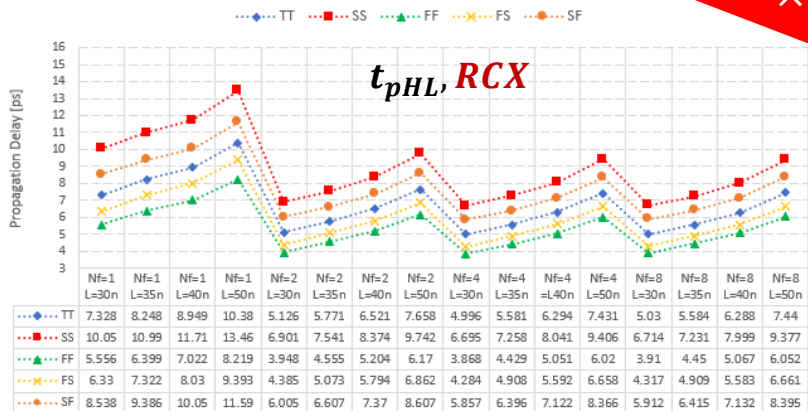
HL Delay VS Nf & L @SVT, VDD=0.9, temp=27 (SCH)



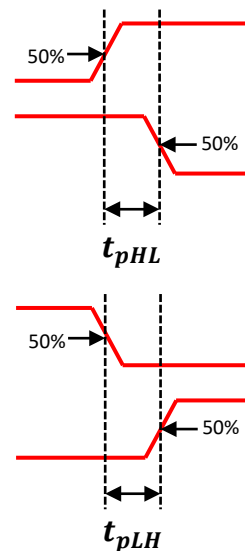
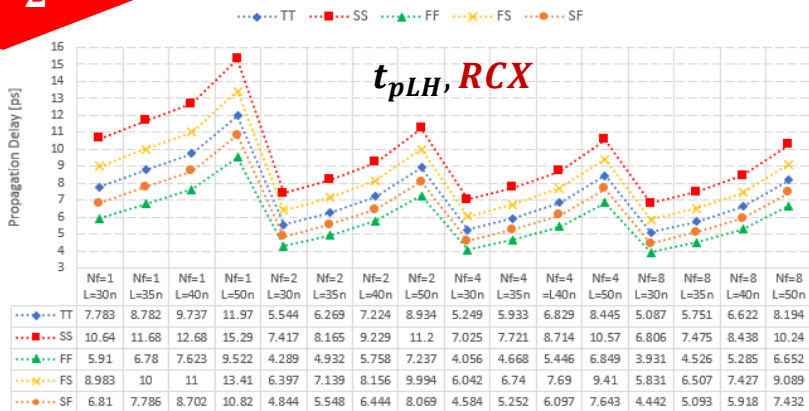
LH Delay VS Nf & L @SVT, VDD=0.9, temp=27 (SCH)



HL Delay VS Nf & L @SVT, VDD=0.9, temp=27 (RCX)



LH Delay VS Nf & L @SVT, VDD=0.9, temp=27 (RCX)

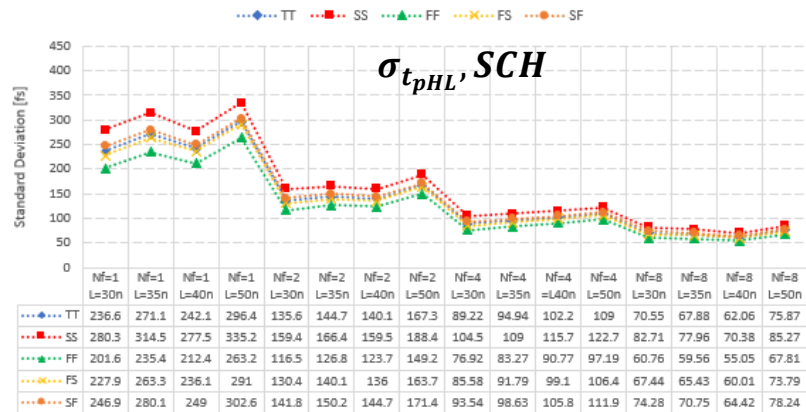


$t_{pSCH} \sim 4ps$

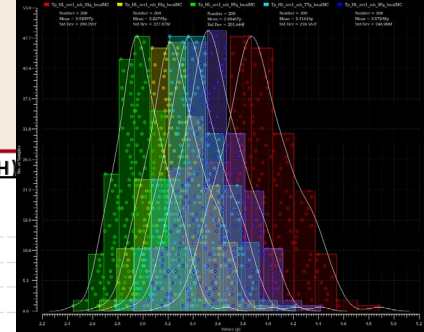
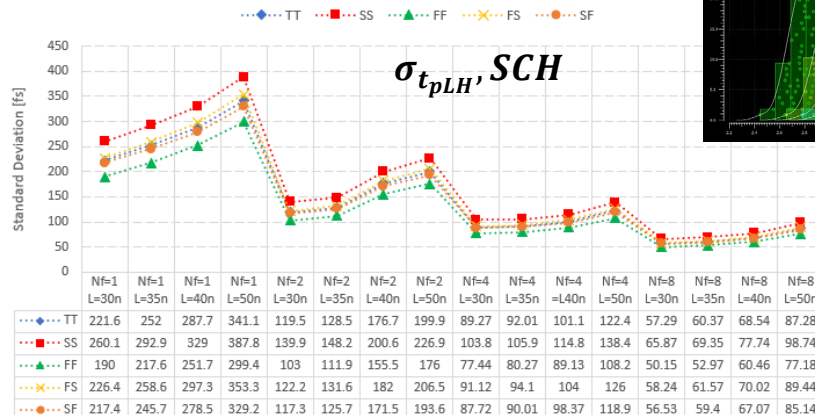
$t_{pRCX} \sim 8ps$

SVT Propagation Delay – Monte Carlo: HL / LH

HL Delay Std VS Nf & L @SVT, VDD=0.9, temp=27 [SCH]



LH Delay Std VS Nf & L @SVT, VDD=0.9, temp=27 [SCH]



Settings:

- Global Corner + Local MC

- 5 corners:

□ TT, 0.9V, 27°C

□ SS, 0.9V, 27°C

□ FF, 0.9V, 27°C

□ FS, 0.9V, 27°C

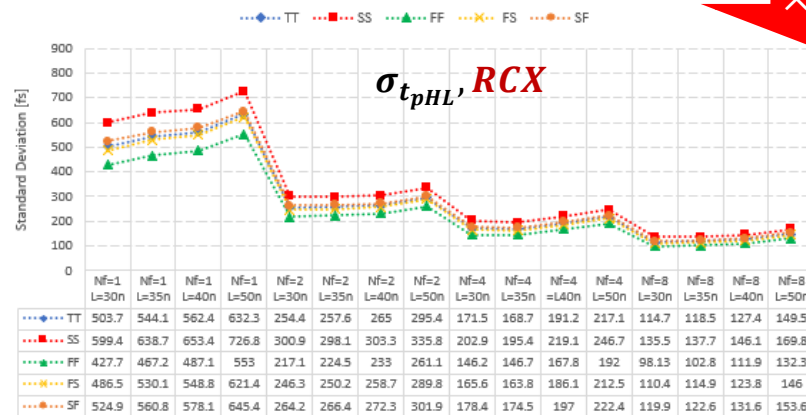
□ SF, 0.9V, 27°C

- N° of runs per corner: 200

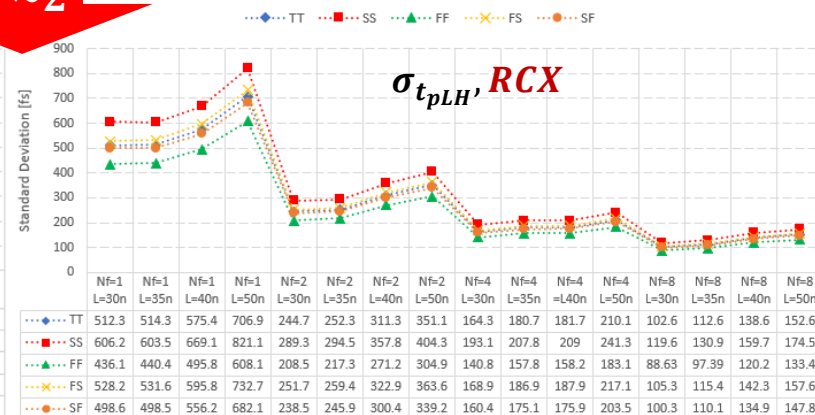
$\sigma_{t_{pSCH}} \sim 200fs$

$\sigma_{t_{pRCX}} \sim 400fs$

HL Delay Std VS Nf & L @SVT, VDD=0.9, temp=27 [RCX]



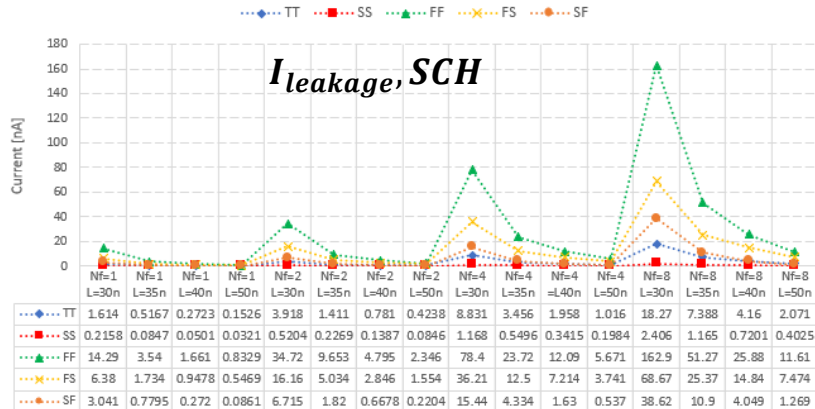
LH Delay Std VS Nf & L @SVT, VDD=0.9, temp=27 [RCX]



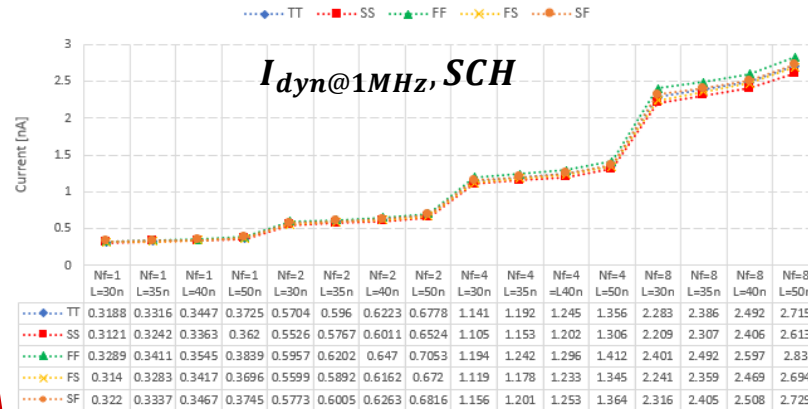
SVT Current Consumption: Leakage / Dynamic@1MHz

TID-ID 

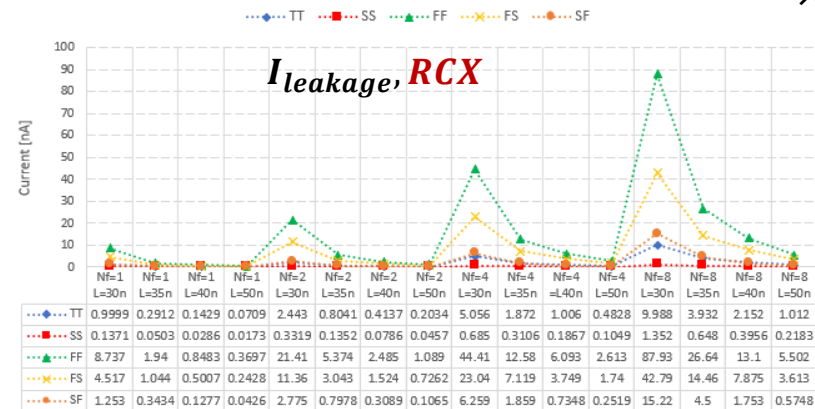
Leakage I VS Nf & L @SVT, VDD=0.9, temp=27 [SCH]



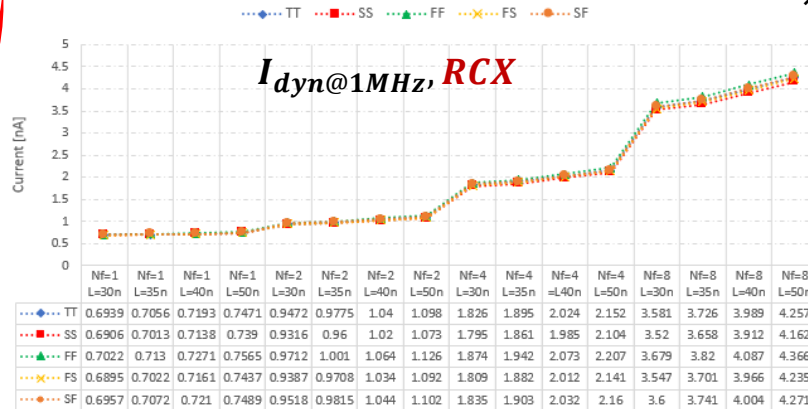
Dynamic I @ 1MHz VS Nf & L @SVT, VDD=0.9, temp=27 [SCH]



Leakage I VS Nf & L @SVT, VDD=0.9, temp=27 [RCX]



Dynamic I @ 1MHz VS Nf & L @SVT, VDD=0.9, temp=27 [RCX]

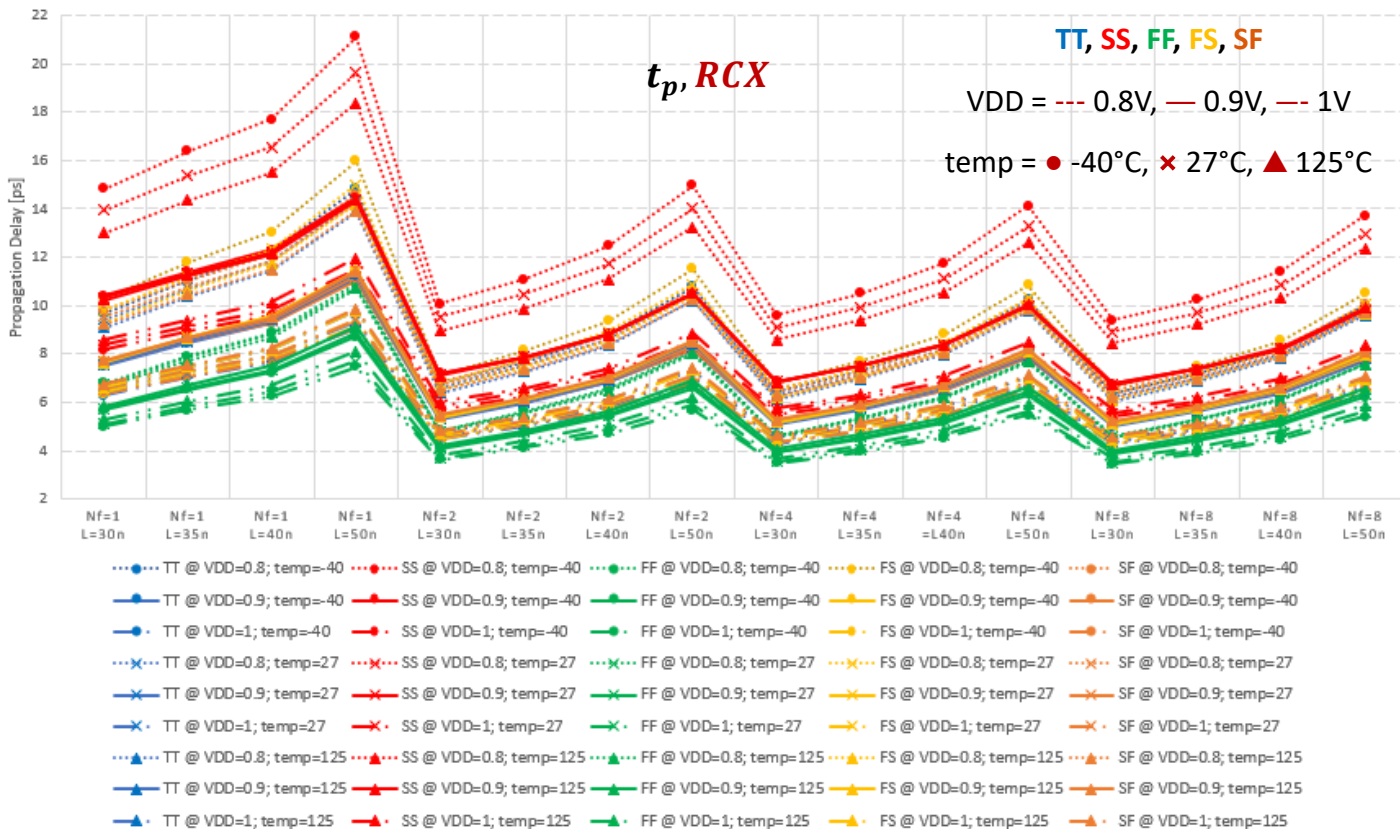


$\times \sim 0.5$

$\times \sim 1.8$

SVT Propagation Delay VS corners, VDD, temp

Delay VS Nf & L @SVT **(RCX)**



$$t_p = \frac{t_{pHL} + t_{pLH}}{2}$$

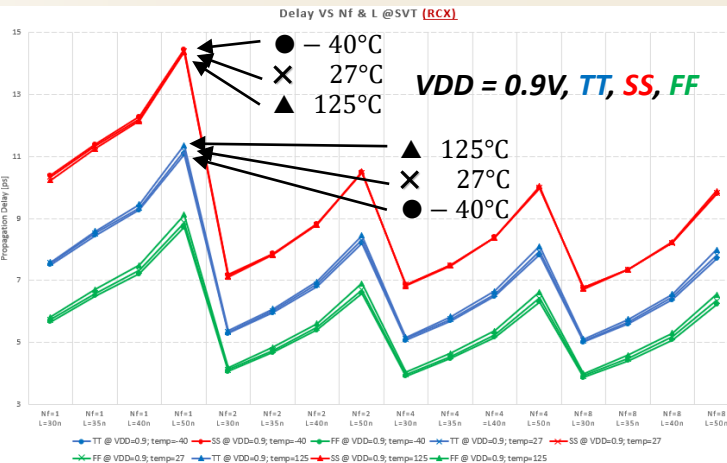
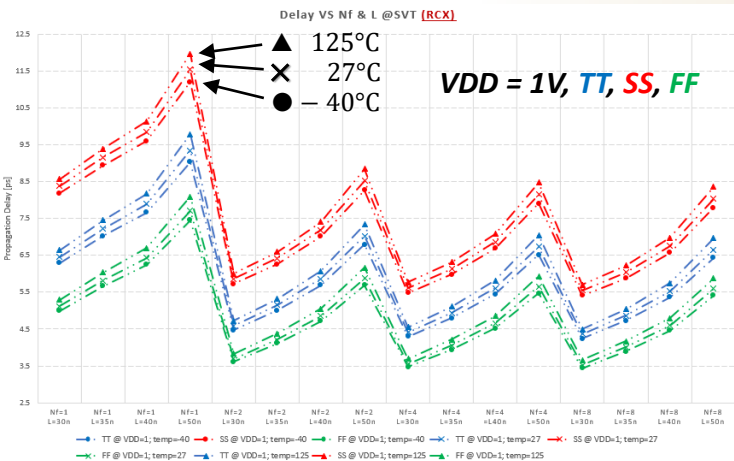
- Best Case (Fastest):
FF @ VDD=1V & -40°C
- Worst Case (Slowest):
SS @ VDD=0.8V & -40°C
[expected: SS @ VDD=0.8V & 125°C]

$$\frac{WorstCase}{Typical} \sim 1.9$$

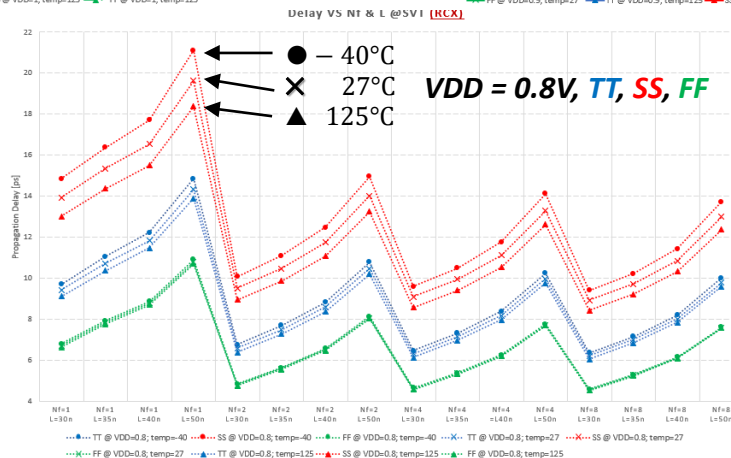
$$\frac{BestCase}{Typical} \sim 0.68$$

- Typical:
TT @ VDD=0.9V & 27°C

SVT Propagation Delay VS corners, VDD, temp



- Very small variation with temperature [especially at VDD=0.9V)] (?)
- At VDD = 0.8V, the delay is higher for lower temperatures [weak inversion effect (?); $I_{diffusion} > I_{drift}$ (?)]

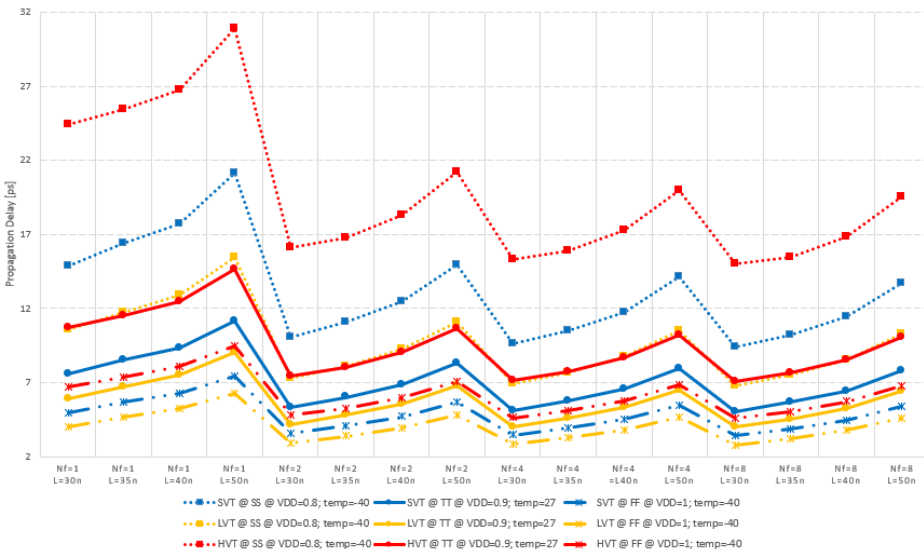


Propagation Delay: SVT, LVT, HVT

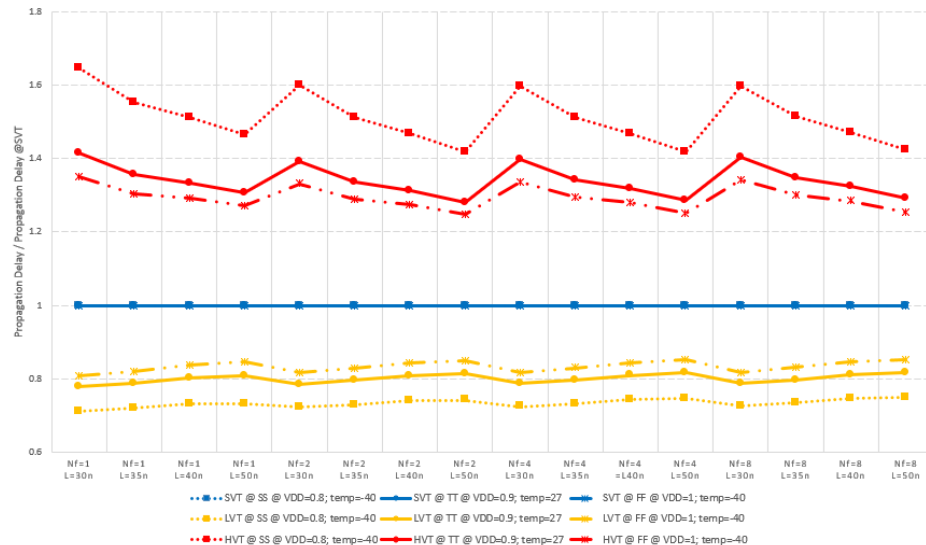
$$t_p, RCX$$

$$\frac{t_p}{t_{p@SVT}}, RCX$$

Delay VS Nf & L (RCX)



Normalized Delay VS Nf & L (RCX)

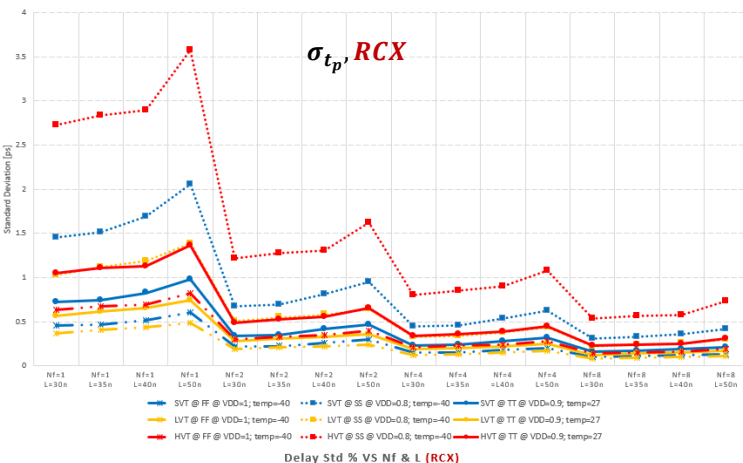


SVT
LVT
HVT

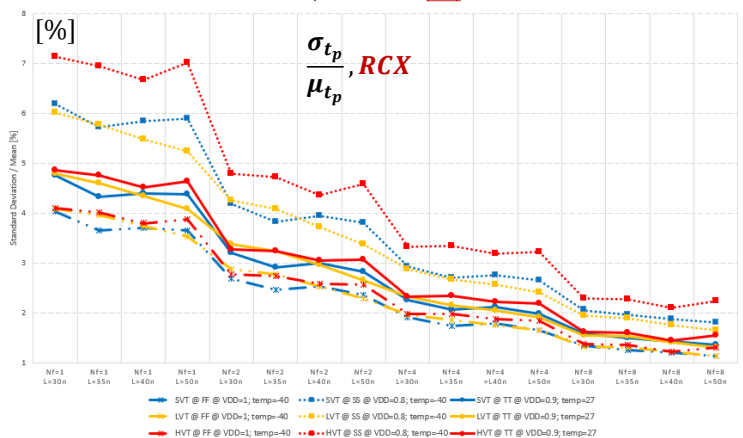
---■ SS; VDD = 0.8V; temp = -40°C
—● TT; VDD = 0.9V; temp = 27°C
---× FF; VDD = 1V; temp = -40°C

Propagation Delay – Monte Carlo: SVT, LVT, HVT

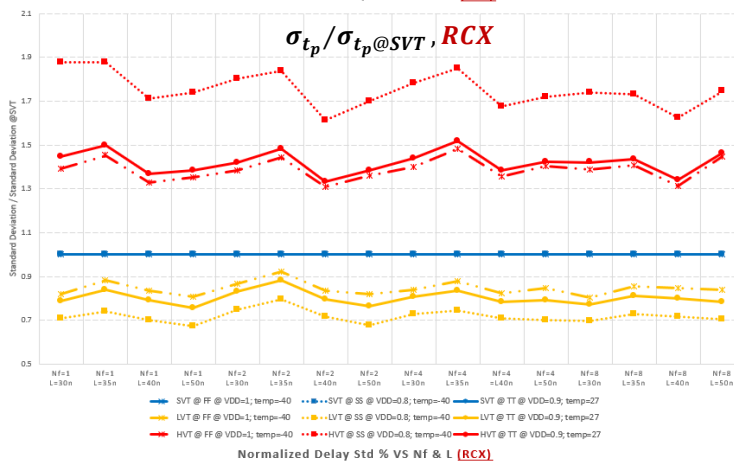
Delay Std VS Nf & L [RCX]



Delay Std % VS Nf & L [RCX]



Normalized Delay Std VS Nf & L [RCX]



Settings:

- Global Corner + Local MC
- 5 corners:
 - TT, 0.9V, 27°C
 - SS, 0.8V, -40°C
 - FF, 1V, -40°C
- N° of runs per corner: 1000

$$\sigma_{tp} = \sqrt{\sigma_{tpHL}^2 + \sigma_{tpLH}^2}$$

- $\frac{\sigma_{tp}}{\mu_{tp}}$ similar (+24%, -11%) for SVT, LVT and HVT structures

SVT
LVT
HVT

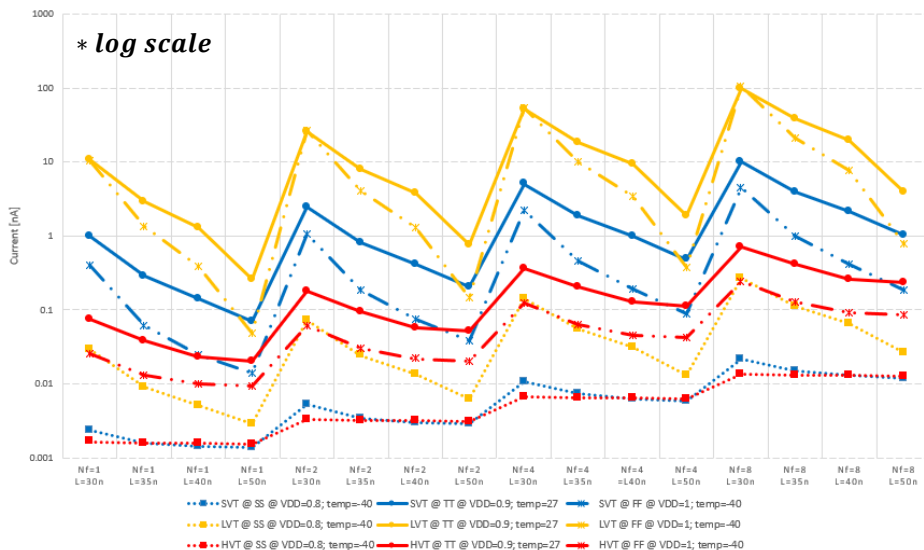
---■ SS; VDD = 0.8V; T = -40°C
—● TT; VDD = 0.9V; T = 27°C
---× FF; VDD = 1V; T = -40°C

Leakage Current: SVT, LVT, HVT

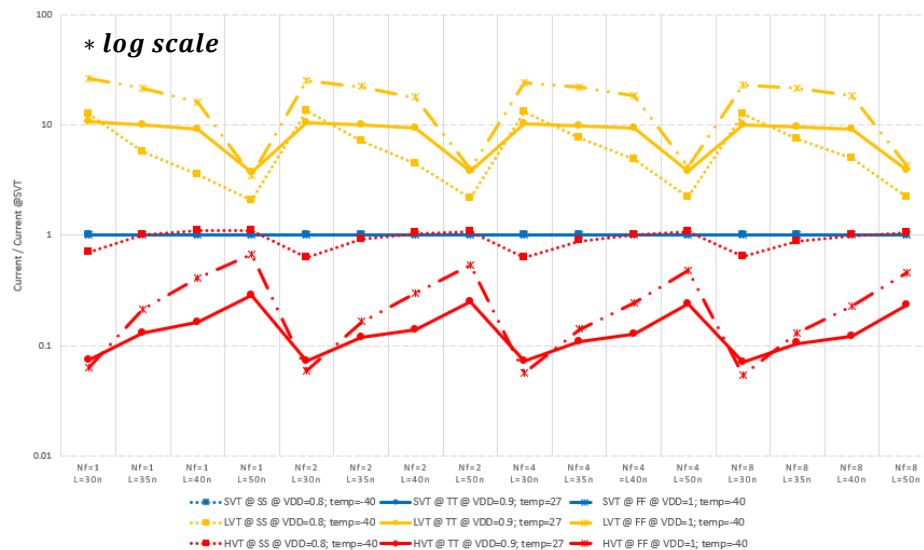
$I_{leakage}, RCX$

$\frac{I_{leakage}}{I_{leakage@SVT}}, RCX$

Leakage I VS Nf & L [RCX]



Normalized Leakage I VS Nf & L [RCX]



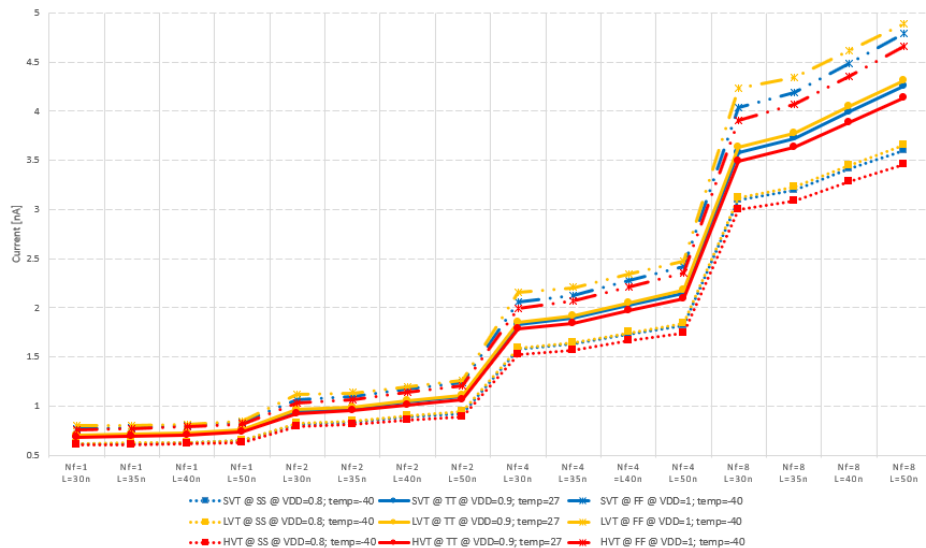
SVT
LVT
HVT

---■ SS; VDD = 0.8V; temp = -40°C
—● TT; VDD = 0.9V; temp = 27°C
---× FF; VDD = 1V; temp = -40°C

Dynamic Current @1MHz: SVT, LVT, HVT

$$I_{dyn@1MHz}, RCX$$

Dynamic I VS Nf & L (RCX)

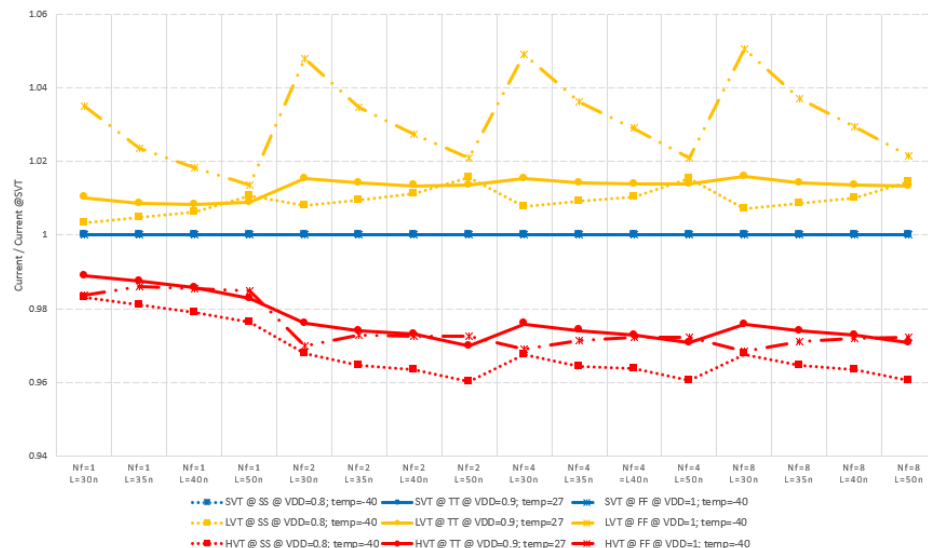


SVT
LVT
HVT

---■ SS; VDD = 0.8V; temp = -40°C
—● TT; VDD = 0.9V; temp = 27°C
---× FF; VDD = 1V; temp = -40°C

$$\frac{I_{dyn@1MHz}}{I_{dyn@1MHz@SVT}}, RCX$$

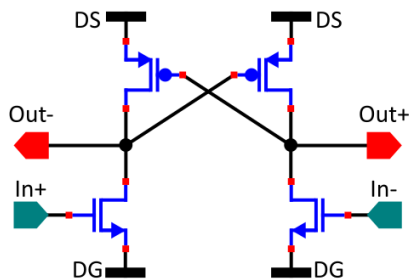
Normalized Dynamic I VS Nf & L (RCX)



- Dynamic consumption very similar (+5%, -4%) for SVT, LVT and HVT structures

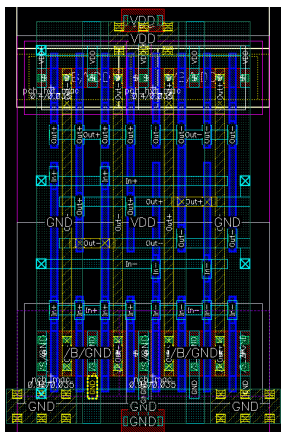
More complex Delay Cells

- ❑ Differential Cascode Voltage Switch Logic (DCVSL) implementation:



Cell variants:

- Cell A: nmos: SVT; pmos: HVT
- Cell B: nmos: LVT; pmos: HVT
- Cell C: nmos: LVT; pmos: SVT
- Cell D: nmos: LVT; pmos: LVT

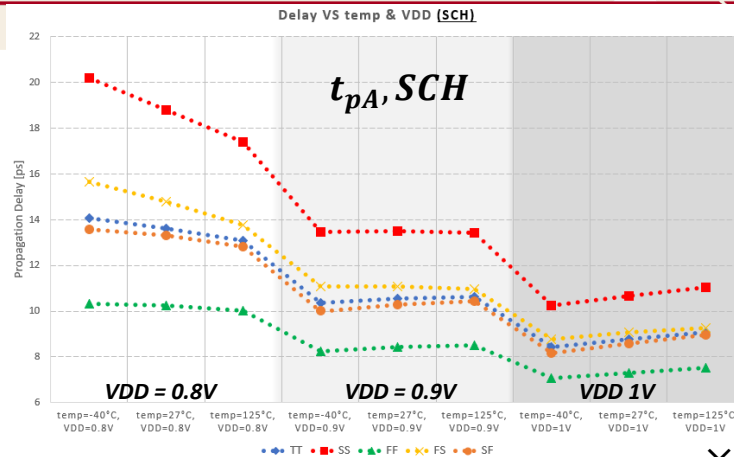


MOS dimensions:

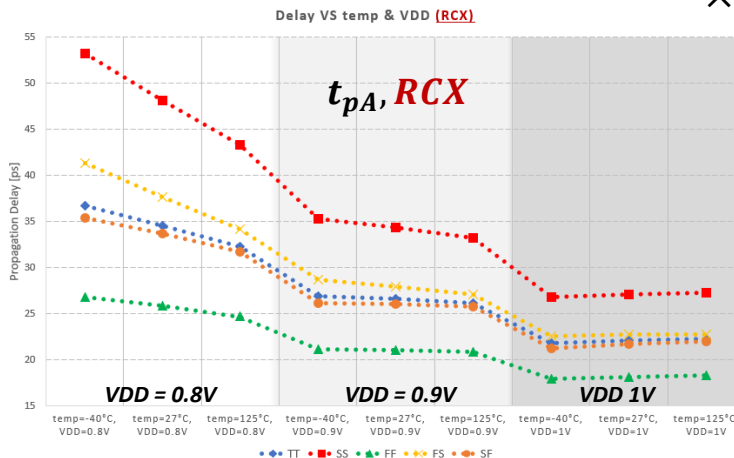
- Wp=100n
- Wn=240n
- L=35n
- Nf=4

Layout:

- M1&M2 – Signal Connections
- M3 – VDD & GND planes covering the cells



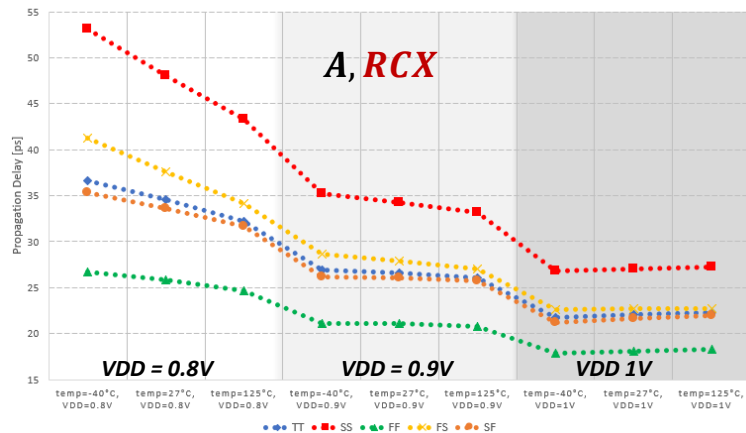
× ~2.5*



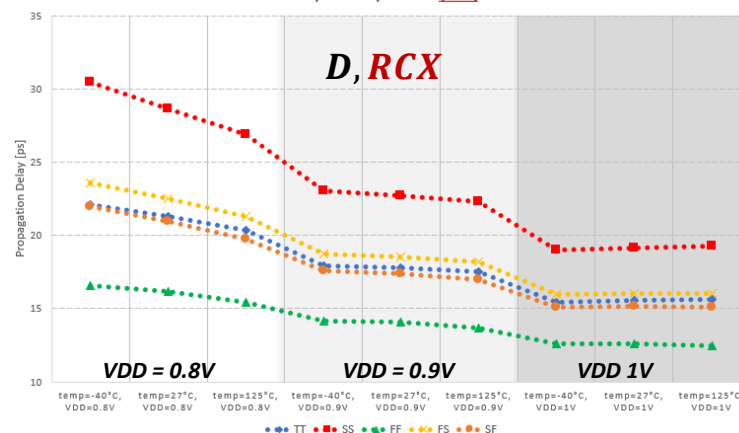
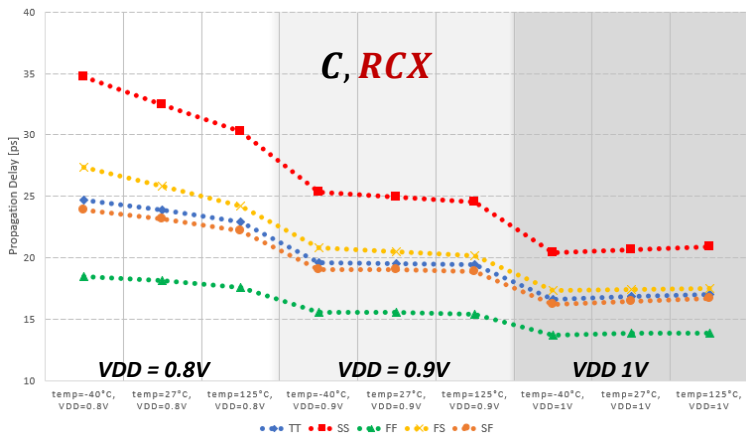
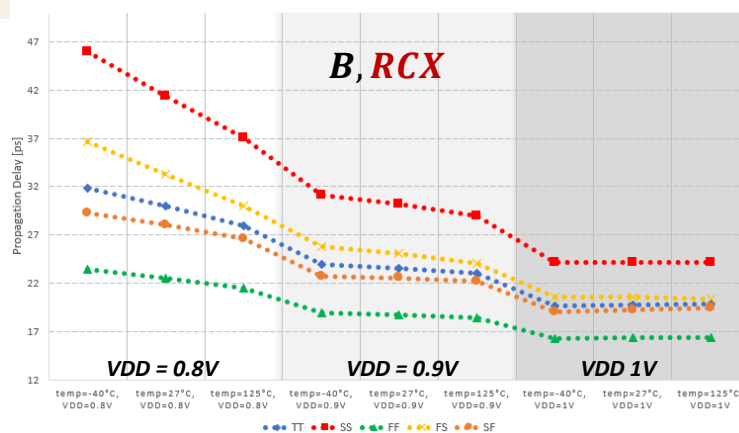
*First layout iteration had propagation delay 3.5x times bigger than in the schematic; parasitics play a big role

More complex Delay Cells: Propagation Delay

Delay VS temp & VDD [RCX]



Delay VS temp & VDD [RCX]



Cell variants:

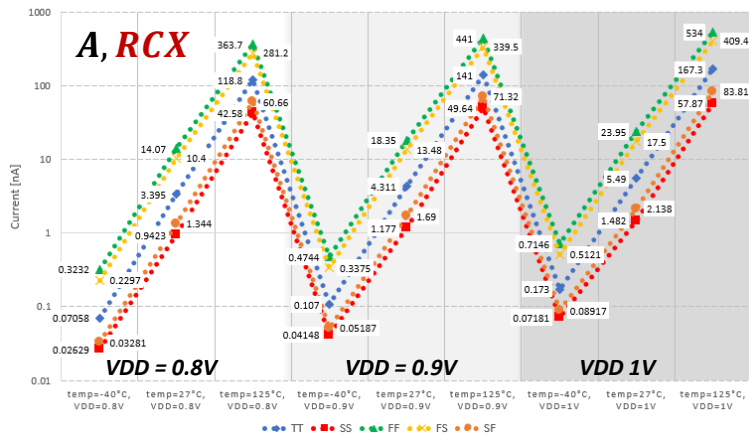
- **Cell A:** nmos: SVT; pmos: HVT
- **Cell B:** nmos: LVT; pmos: HVT
- **Cell C:** nmos: LVT; pmos: SVT
- **Cell D:** nmos: LVT; pmos: LVT

Very low propagation delay dependance on temperature

More complex Delay Cells: Leakage Current

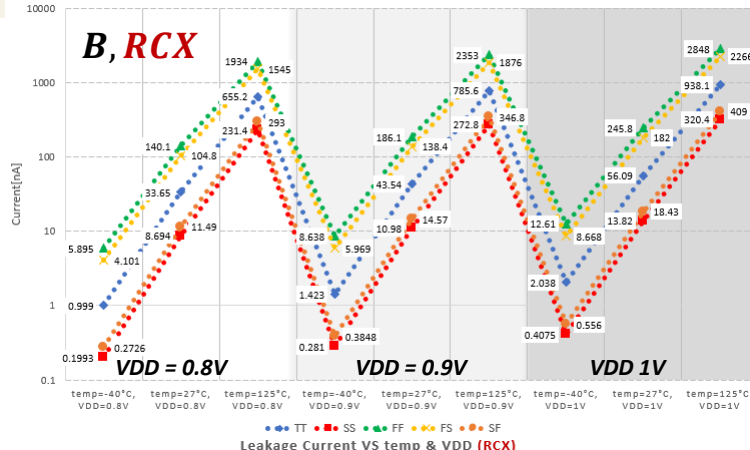
Leakage Current VS temp & VDD (RCX)

A, RCX



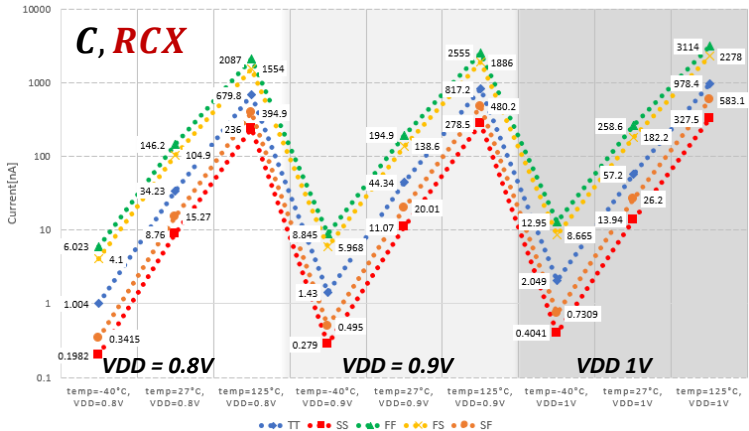
Leakage Current VS temp & VDD (RCX)

B, RCX



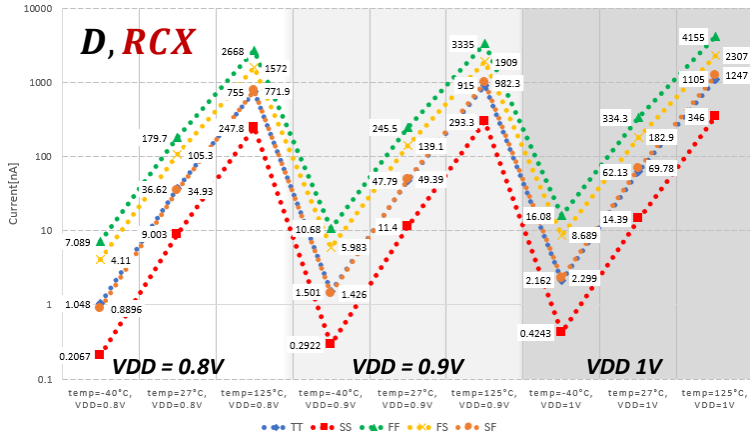
Leakage Current VS temp & VDD (RCX)

C, RCX



Leakage Current VS temp & VDD (RCX)

D, RCX



Cell variants:

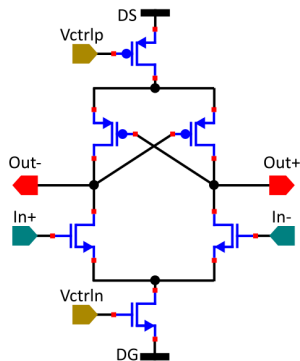
- Cell A: nmos: SVT; pmos: HVT
- Cell B: nmos: LVT; pmos: HVT
- Cell C: nmos: LVT; pmos: SVT
- Cell D: nmos: LVT; pmos: LVT

Very high leakage current dependance on temperature

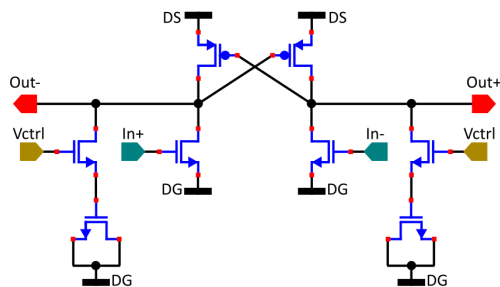
Voltage-Controlled Delay Cells – Quick Comparison

TID-ID **SI AG**

Current-Starved Delay Cell:

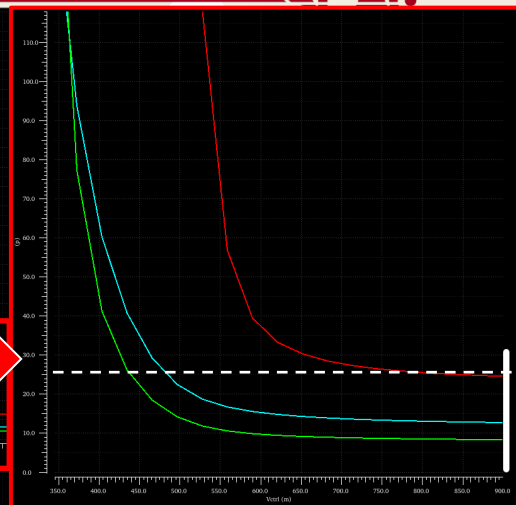
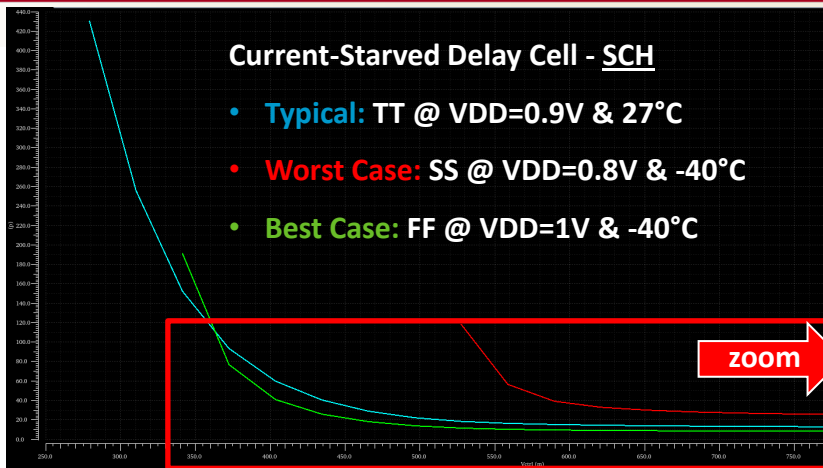


Shunt-Capacitor Delay Cell:



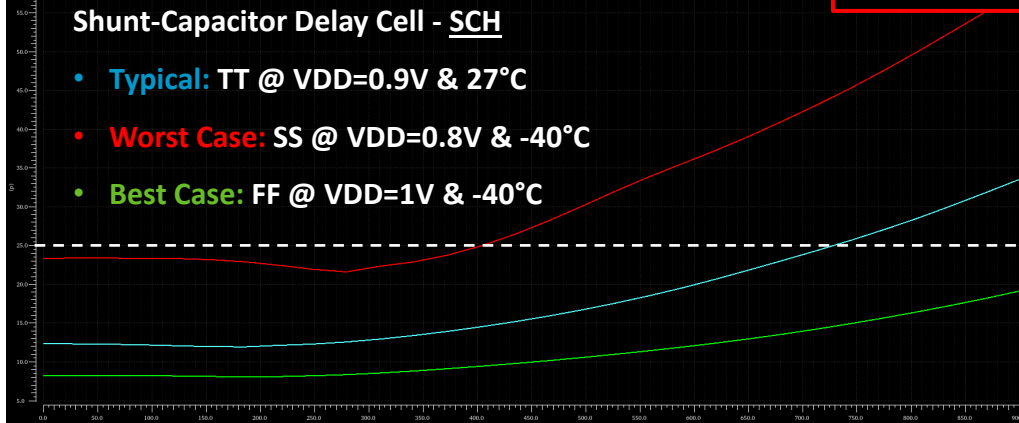
Current-Starved Delay Cell - SCH

- **Typical:** TT @ VDD=0.9V & 27°C
- **Worst Case:** SS @ VDD=0.8V & -40°C
- **Best Case:** FF @ VDD=1V & -40°C



Shunt-Capacitor Delay Cell - SCH

- **Typical:** TT @ VDD=0.9V & 27°C
- **Worst Case:** SS @ VDD=0.8V & -40°C
- **Best Case:** FF @ VDD=1V & -40°C



Next Steps

- ☐ Design and layout of Current-Starved and Shunt-Capacitor delay cells (different variants)
- ☐ Performance comparison between CS and SC approaches
- ☐ Schematic and layout optimization of the chosen Voltage-Controlled Delay Cell
- ☐ TDC architecture definition & design